

NOV. 21. 2002 4:21PM

KON PEABODY

NO. 4488 P. 1/3

Nixon Peabody LLP

Attorneys at Law

8180 Greensboro Drive
Suite 800
McLean, Virginia 22102-3823
(703) 770-9300

Fax: (703) 770-9400

PRIVILEGE AND CONFIDENTIALITY NOTICE

The information in this fax is intended for the named recipients only. It contains privileged and confidential matter. If you have received this fax in error, please notify us immediately by a collect telephone call to (703) 770-9300 and return the original to the sender by mail. We will reimburse you for postage. Do not disclose the contents to anyone. Thank you.

FAX

1013
12/21/02
amr

Date: November 21, 2002

Pages (including cover): 3

To: April Wise

Fax: 703.746.8822

Ph:

From: Donald R. Studebaker

Message: RE: U.S. Patent Application No. 09/865,546

Dear Ms. Wise:

In response to the Notice of Non-Compliant Amendment, attached please find a clean version of the paragraph in question in connection with the Amendment filed October 1, 2002.

Application No.: 09/865,546
Attorney Docket No.: 740819-560
Art Unit 2829
Page 4

On page 9, please replace the final paragraph abridging pages 9 and 10 with the following substitute paragraph. Attached hereto is a marked-up copy of the substitute paragraph.

N/E
--In the second semiconductor device, the heavily-doped diffusion layer preferably corresponds to a pocket heavily-doped diffusion layer of a MIS semiconductor device, and the MIS semiconductor device preferably includes a gate electrode formed above the semiconductor substrate with a gate insulating film sandwiched therebetween; a source/drain heavily-doped diffusion layer of a first conductivity type formed in a source/drain region of the semiconductor substrate at a distance from a region below a side face of the gate electrode; an extension region heavily-doped diffusion layer of the first conductivity type formed in the semiconductor substrate between the source/drain heavily-doped diffusion layer and the region below the side face of the gate electrode and having shallower junction than the source/drain heavily-doped diffusion layer; and the pocket region of heavily-doped diffusion layer of a second conductivity type formed in the semiconductor substrate under the extension heavily-doped diffusion layer.--

On page 10, please replace the first full paragraph with the following substitute paragraph. Attached hereto is a marked-up copy of the substitute paragraph.

--In this case, the extension region heavily-doped diffusion layer is preferably formed by using an antimony ion as a dopant.--

On page 10, please replace the third full paragraph with the following substitute paragraph. Attached hereto is a marked-up copy of the substitute paragraph.

B'
--Since a pocket region of heavily-doped diffusion layer is formed by implantation and

Application No.: 09/865,546
Attorney Docket No.: 740819-560
Art Unit 2829
Page 5

Benix

diffusion of the dopant heavy ion in the epitaxial region of silicon in the first method for fabricating a semiconductor device, the heavy ion is minimally segregated in the region below the original amorphous-crystal interface. Accordingly, the semiconductor device can be refined with a leakage current derived from the segregation suppressed.--

On page 11, please replace the second full paragraph with the following substitute paragraph. Attached hereto is a marked-up copy of the substitute paragraph.

N.E.

--In the first method for fabricating a semiconductor device, the heavily-doped diffusion layer is preferably formed by using, as the dopant ion, an indium ion at a dose of $5 \times 10^3/\text{cm}^2$ or more. Since the first dopant layer can be thus changed into an amorphous layer, the channeling of the second dopant subsequently implanted can be suppressed. Accordingly, the extension region heavily-doped diffusion layer and the pocket region of heavily-doped diffusion layer can definitely attain shallow junction, resulting in realizing a semiconductor device with high driving power.--

On page 11, please replace the final paragraph abridging pages 11 and 12 with the following substitute paragraph. Attached hereto is a marked-up copy of the substitute paragraph.

--In the first method for fabricating a semiconductor device, the heavily-doped diffusion layer preferably corresponds to a pocket region of heavily-doped diffusion layer of a MIS semiconductor device, and the method for fabricating the MIS semiconductor device preferably includes the steps of forming a gate electrode above the epitaxial region with a gate insulating film sandwiched therebetween; forming a first dopant layer to be used as the pocket region of

NYA240867.1